

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	37469	438/6,10,104,107,108,109,110,111,112,113,114,118,121,122,123,128,129,135,142,145,149,151,157,176,478,184,193,195,196,197,198,200,201,202,203,206,207,209,210,211,218,237,165,248,268,343,294,308,337,353,378,401,410,5,7,11,14,16,17,18,22,23,24,29,31,34,35,36,130,484,538.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 00:07
L2	4	I1 and method and semiconductor near device and first near group near3 gate near2 electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 00:08
L3	2	I2 and second near2 group near3 gate near electrode and ((first near2 region) same (second near2 region))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 00:10
L4	0	I2 and second near2 group near3 gate near electrode and ((first near2 region) same (second near2 region)) and planarizing near3 first near2 dielectric near2 film	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 00:11
S88	14451	438/5,7,10,11,14,16,17,18,22,23,24,29,31,34,35,36,128,129,130,149,484,538.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 19:29
S108	6	(US-20050029583-\$ or US-20040087114-\$).did. or (US-6855588-\$ or US-6847084-\$ or US-6645797-\$ or US-5846734-\$).did.	US-PGPUB; USPAT	OR	ON	2006/01/10 12:04